

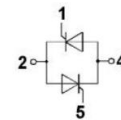
## PRODUCT FEATURES

- Compact Design
- One screw mounting
- Heat transfer and isolation through DBC
- Glass passivation thyristor chips
- Low Leakage Current



## APPLICATIONS

- Soft starters
- Temperature control
- Light control



## ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Test Conditions	Values	Unit
V <sub>RRM</sub>	Maximum Repetitive Reverse Voltage	T <sub>vj</sub> =125°C	1200	V
V <sub>DRM</sub>	Maximum repetitive peak off-state voltage			
V <sub>RSM</sub>	Non-Repetitive Reverse Voltage	T <sub>vj</sub> =125°C	1300	V
V <sub>DSM</sub>	Non-repetitive peak off-state voltage			
I <sub>RRM</sub>	Maximum Repetitive Reverse Current	T <sub>vj</sub> =125°C	5	mA
I <sub>DRM</sub>	Maximum repetitive peak off-state Current			
I <sub>T(AV)</sub>	Mean On-state Current	T <sub>c</sub> =85°C	55	A
I <sub>T(RMS)</sub>	RMS Current	T <sub>c</sub> =85°C, sin180°	80	
I <sub>TSM</sub>	Non Repetitive Surge Peak On-state Current	10ms, T <sub>j</sub> =25°C	1100	
I <sup>2</sup> t	For Fusing	10ms, T <sub>j</sub> =25°C	6050	A <sup>2</sup> S
V <sub>TM</sub>	Peak on-state voltage	I <sub>TM</sub> =150A	1.7	V
dv/dt	critical rate of rise of off-state voltage	V <sub>D</sub> =2/3V <sub>DRM</sub> Gate Open T <sub>j</sub> =125°C	1000	V/us
I <sub>GT</sub>	gate trigger current max.		80	mA
V <sub>GT</sub>	gate trigger voltage max.		1.5	V
I <sub>H</sub>	gate trigger current		200	mA
I <sub>L</sub>	latching current		500	mA
Viso	AC 50Hz RMS 1min		2500	V
T <sub>J</sub>	Junction Temperature		-40 to +125	°C
T <sub>STG</sub>	Storage Temperature Range		-40 to +125	
R <sub>thJC</sub>	Junction to Case Thermal Resistance(Per thyristor chip )		0.7	°C /W
Torque	mounting force, Module to Sink		2.5	Nm
Tsolder	Teminals,10s		260	°C

Outlines

